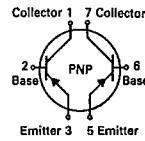
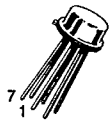


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**2N3806, A  
thru  
2N3811, A**

CASE 654-07, STYLE 1



2N3810, 2N3811 — JAN, JTX, JTXV  
AVAILABLE

**DUAL  
AMPLIFIER TRANSISTORS**

PNP SILICON



**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	60	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current — Continuous	I <sub>C</sub>	50	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	One Die	mW
		Both Die	mW
			mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)**

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage(1) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	60	—	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	—	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	—	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	—	0.01 10	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 4.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	—	20	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain(1) (I <sub>C</sub> = 1.0 μAdc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	2N3807,9,11,A	75	—
(I <sub>C</sub> = 10 μAdc, V <sub>CE</sub> = 5.0 Vdc)			100	—
			225	—
(I <sub>C</sub> = 100 μAdc, V <sub>CE</sub> = 5.0 Vdc)			150	450
			300	900
(I <sub>C</sub> = 100 μAdc, V <sub>CE</sub> = 5.0 Vdc, T <sub>A</sub> = -55°C)			75	—
			150	—
(I <sub>C</sub> = 500 μAdc, V <sub>CE</sub> = 5.0 Vdc)			150	450
	300	900		
(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc)	150	450		
	300	900		
(I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc)	125	—		
	250	—		
Collector-Emitter Saturation Voltage(1) (I <sub>C</sub> = 100 μAdc, I <sub>B</sub> = 1.0 μA) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 100 μAdc)	V <sub>CE(sat)</sub>	—	0.2 0.25	Vdc
Base-Emitter Saturation Voltage(1) (I <sub>C</sub> = 100 μAdc, I <sub>B</sub> = 10 μAdc) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 100 μAdc)	V <sub>BE(sat)</sub>	—	0.7 0.8	Vdc

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**ELECTRICAL CHARACTERISTICS** (continued) ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Base-Emitter On Voltage ( $I_C = 100 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	$V_{BE(on)}$	—	0.7	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Current-Gain — Bandwidth Product ( $I_C = 500 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $f = 30 \text{ MHz}$ ) ( $I_C = 1.0 \text{ mA}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $f = 100 \text{ MHz}$ )	$f_T$	30 100	— 500	MHz
Output Capacitance ( $V_{CB} = 5.0 \text{ Vdc}$ , $I_E = 0$ , $f = 100 \text{ kHz}$ )	$C_{obo}$	—	4.0	pF
Input Capacitance ( $V_{BE} = 0.5 \text{ Vdc}$ , $I_C = 0$ , $f = 100 \text{ kHz}$ )	$C_{ibo}$	—	8.0	pF
Input Impedance ( $I_C = 1.0 \text{ mA}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	$h_{ie}$	3.0 10	30 40	k $\Omega$
Voltage Feedback Ratio ( $I_C = 1.0 \text{ mA}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	$h_{re}$	—	25	$\times 10^{-4}$
Small-Signal Current Gain ( $I_C = 1.0 \text{ mA}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	$h_{fe}$	150 300	600 900	—
Output Admittance ( $I_C = 1.0 \text{ mA}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	$h_{oe}$	5.0	60	$\mu\text{mhos}$
Noise Figure ( $I_C = 100 \mu\text{A}$ , $V_{CE} = 10 \text{ Vdc}$ , $R_G = 3.0 \text{ kohms}$ $f = 100 \text{ Hz}$ , $BW = 20 \text{ Hz}$ )	NF	—	7.0 4.0	dB
Spot Noise $f = 1.0 \text{ kHz}$ , $BW = 200 \text{ Hz}$		—	3.0 1.5	
$f = 10 \text{ kHz}$ , $BW = 2.0 \text{ kHz}$		—	2.5 1.5	
Broadband Noise Bandwidth 10 Hz to 15.7 kHz		—	3.5 2.5	

**MATCHING CHARACTERISTICS**

DC Current Gain Ratio(2) ( $I_C = 100 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	$h_{FE1}/h_{FE2}$	0.8 0.9 0.95	1.0 1.0 1.0	—
( $I_C = 100 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $T_A = -55 \text{ to } +125^\circ\text{C}$ )		0.85	1.0	
Base-Emitter Voltage Differential ( $I_C = 10 \mu\text{A}$ to $10 \text{ mA}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	$ V_{BE1} - V_{BE2} $	—	8.0 5.0	mVdc
( $I_C = 100 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ )		—	5.0 3.0 1.5	
Base-Emitter Voltage Differential Change Due to Temperature ( $I_C = 100 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $T_A = -55 \text{ to } +25^\circ\text{C}$ )	$\Delta(V_{BE1} - V_{BE2})$	—	1.6 0.8 0.4	mVdc
( $I_C = 100 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $T_A = +25 \text{ to } +125^\circ\text{C}$ )		—	2.0 1.0 0.5	

(1) Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .  
 (2) The lowest  $h_{FE}$  reading is taken as  $h_{FE1}$  for this ratio.

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FIGURE 1 — DC CURRENT GAIN versus COLLECTOR CURRENT

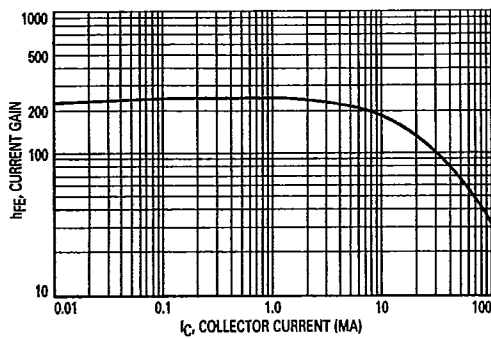


FIGURE 2 — DC CURRENT GAIN versus COLLECTOR CURRENT

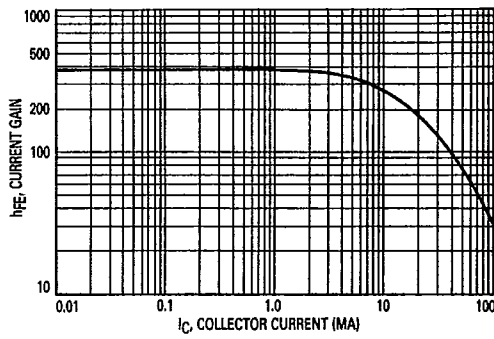


FIGURE 3 — "ON" VOLTAGES

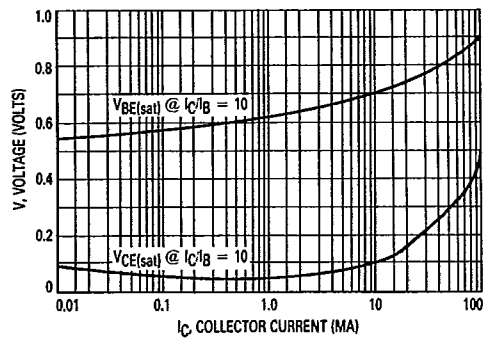
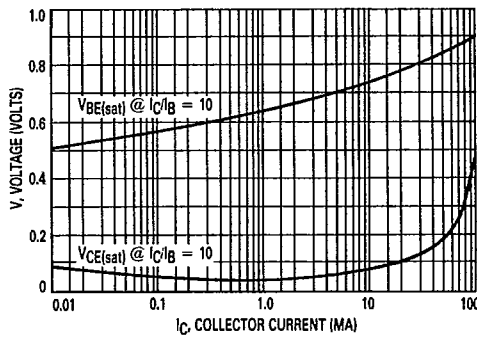


FIGURE 4 — "ON" VOLTAGES



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